To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SK2586

Silicon N-Channel MOS FET

ADE-208-358C (Z)
4th. Edition
Aug. 1995

Application

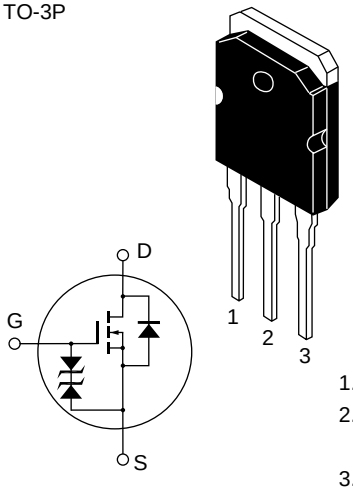
High speed power switching

Features

- Low on-resistance
- $R_{DS(on)}$ = 7 m typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

Outline

TO-3P



1. Gate
2. Drain
   (Flange)
3. Source

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D *2	60	A
Drain peak current	$I_{D(pulse)}$ *1	240	A
Body to drain diode reverse drain current	I_{DR} *2	60	A
Avalanche current	I_{AP} *3	45	A
Avalanche energy	E_{AR} *3	174	mJ
Channel dissipation	Pch*2	125	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW 10 µs, duty cycle 1 %
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg 50

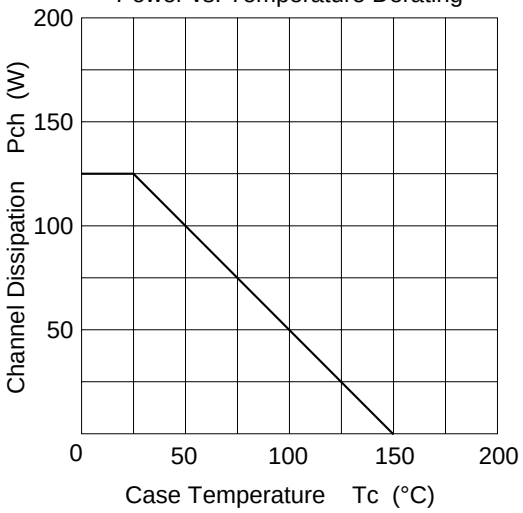
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±16 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	100	µA	V_{DS} = 60 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	I_D = 1 mA, V_{DS} = 10 V
Static drain to source on state resistance	$R_{DS(on)}$	—	7	10	m	I_D = 30 A V_{GS} = 10 V*[1]
		—	10	16	m	I_D = 30 A V_{GS} = 4 V*[1]
Forward transfer admittance	$\|y_{fs}\|$	35	60	—	S	I_D = 30 A V_{DS} = 10 V*[1]
Input capacitance	Ciss	—	3550	—	pF	V_{DS} = 10 V
Output capacitance	Coss	—	1760	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	500	—	pF	f = 1 MHz
Turn-on delay time	$t_{d(on)}$	—	35	—	ns	I_D = 30 A
Rise time	t_r	—	260	—	ns	V_{GS} = 10 V
Turn-off delay time	$t_{d(off)}$	—	480	—	ns	R_L = 1.0
Fall time	t_f	—	370	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.94	—	V	I_F = 60 A, V_{GS} = 0
Body to drain diode reverse recovery time	t_{rr}	—	140	—	ns	I_F = 60 A, V_{GS} = 0 diF / dt = 50 A / µs

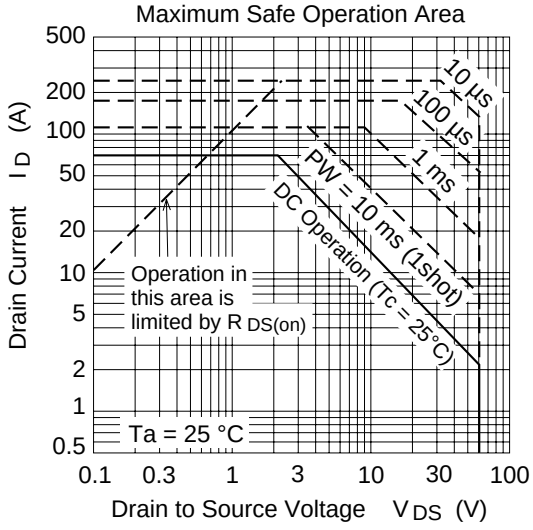
Note: 1. Pulse Test

See characteristic curves of 2SK2529.

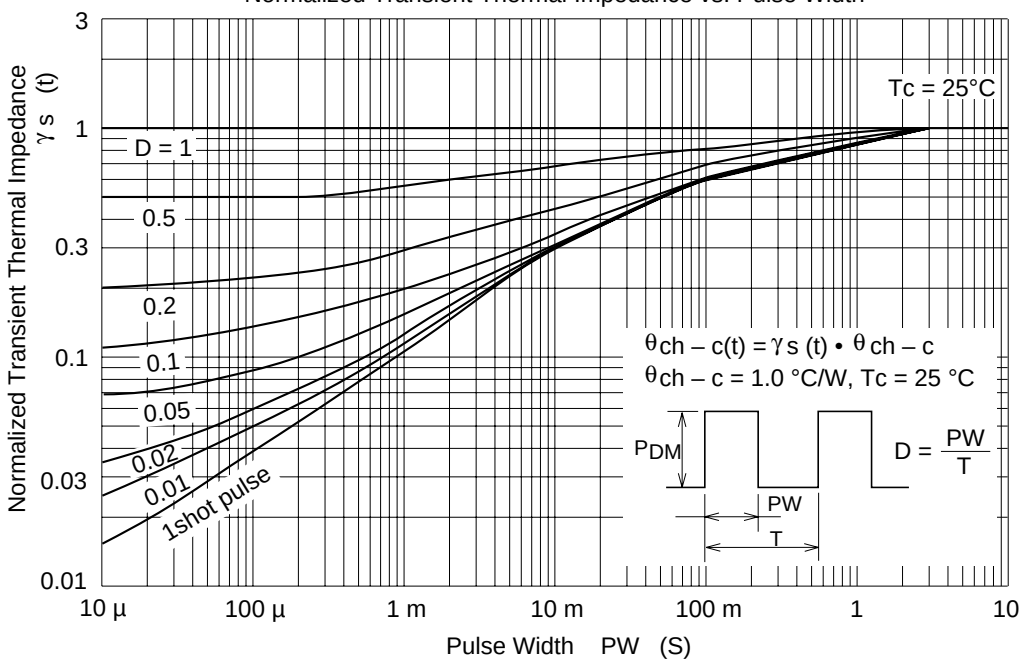
Power vs. Temperature Derating



Maximum Safe Operation Area



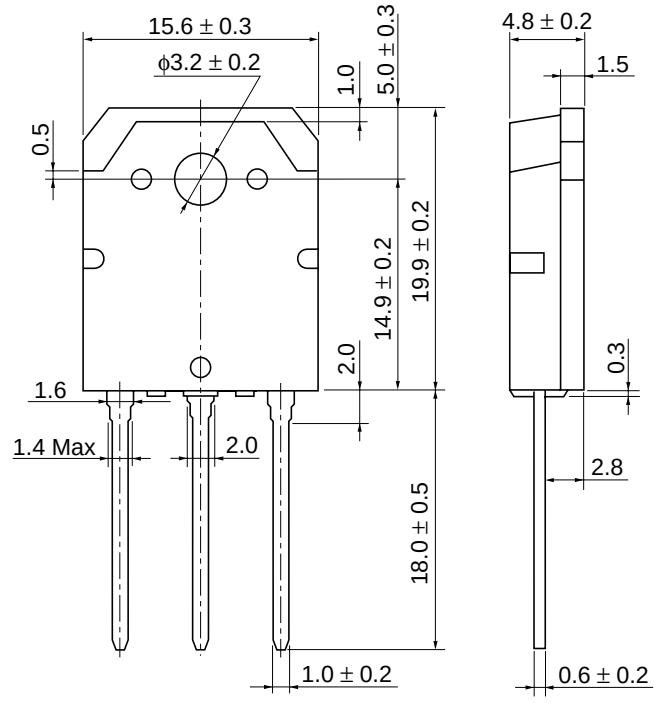
Normalized Transient Thermal Impedance vs. Pulse Width

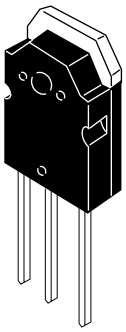


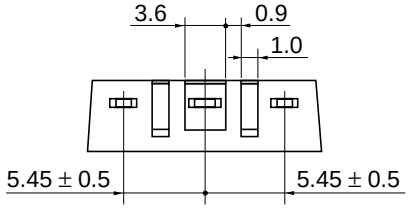
Package Dimensions

As of January, 2001

Unit: mm







Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
NorthAmerica : http://semiconductor.hitachi.com/
Europe : http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straβe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : http://www.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : http://www.hitachi.com.hk

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